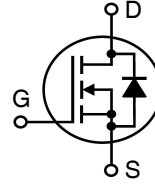


**Q3-Class  
HiperFET™  
Power MOSFET**

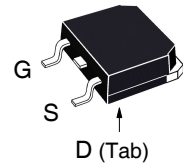
**IXFT18N100Q3  
IXFH18N100Q3**

**V<sub>DSS</sub> = 1000V**  
**I<sub>D25</sub> = 18A**  
**R<sub>DS(on)</sub> ≤ 660mΩ**

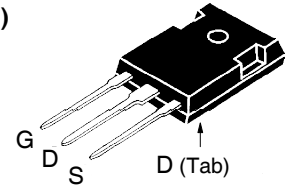
N-Channel Enhancement Mode  
 Avalanche Rated  
 Fast Intrinsic Rectifier



**TO-268  
(IXFT)**



**TO-247  
(IXFH)**



G = Gate      D = Drain  
 S = Source    Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V <sub>DSS</sub>	T <sub>J</sub> = 25°C to 150°C	1000	V
V <sub>DGR</sub>	T <sub>J</sub> = 25°C to 150°C, R <sub>GS</sub> = 1MΩ	1000	V
V <sub>GSS</sub>	Continuous	± 30	V
V <sub>GSM</sub>	Transient	± 40	V
I <sub>D25</sub>	T <sub>C</sub> = 25°C	18	A
I <sub>DM</sub>	T <sub>C</sub> = 25°C, Pulse Width Limited by T <sub>JM</sub>	60	A
I <sub>A</sub>	T <sub>C</sub> = 25°C	18	A
E <sub>AS</sub>	T <sub>C</sub> = 25°C	1.5	J
dv/dt	I <sub>S</sub> ≤ I <sub>DM</sub> , V <sub>DD</sub> ≤ V <sub>DSS</sub> , T <sub>J</sub> ≤ 150°C	50	V/ns
P <sub>D</sub>	T <sub>C</sub> = 25°C	830	W
T <sub>J</sub>		-55 ... +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 ... +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering	300	°C
T <sub>SOLD</sub>	1.6 mm (0.062in.) from Case for 10s	260	°C
M <sub>d</sub>	Mounting Torque (TO-247)	1.13 / 10	Nm/lb.in.
Weight	TO-268	4.0	g
	TO-247	6.0	g

**Features**

- Low Intrinsic Gate Resistance
- International Standard Packages
- Low Package Inductance
- Fast Intrinsic Rectifier
- Low R<sub>DS(on)</sub> and Q<sub>G</sub>

**Advantages**

- High Power Density
- Easy to Mount
- Space Savings

**Applications**

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- DC Choppers
- Temperature and Lighting Controls

Symbol	Test Conditions (T <sub>J</sub> = 25°C Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA	1000		V
V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 4mA	3.5		6.5 V
I <sub>GSS</sub>	V <sub>GS</sub> = ±30V, V <sub>DS</sub> = 0V			±100 nA
I <sub>DSS</sub>	V <sub>DS</sub> = V <sub>DSS</sub> , V <sub>GS</sub> = 0V T <sub>J</sub> = 125°C			25 μA 1.25 mA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.5 • I <sub>D25</sub> , Note 1			660 mΩ

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 20\text{V}, I_D = 0.5 \cdot I_{D25}$ , Note 1	9	16	S
$C_{iss}$	} $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		4890	pF
$C_{oss}$			400	pF
$C_{rss}$			34	pF
$R_{Gi}$	Gate Input Resistance		0.20	$\Omega$
$t_{d(on)}$	} <b>Resistive Switching Times</b> $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 3\Omega$ (External)		37	ns
$t_r$			32	ns
$t_{d(off)}$			40	ns
$t_f$			13	ns
$Q_{g(on)}$	} $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		90	nC
$Q_{gs}$			33	nC
$Q_{gd}$			37	nC
$R_{thJC}$				0.15 $^\circ\text{C/W}$
$R_{thCS}$	TO-247		0.21	$^\circ\text{C/W}$

**Source-Drain Diode**

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			18 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			72 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{V}$ , Note 1			1.4 V
$t_{rr}$	} $I_F = 9\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$			300 ns
$I_{RM}$			11.0	A
$Q_{RM}$			1.5	$\mu\text{C}$

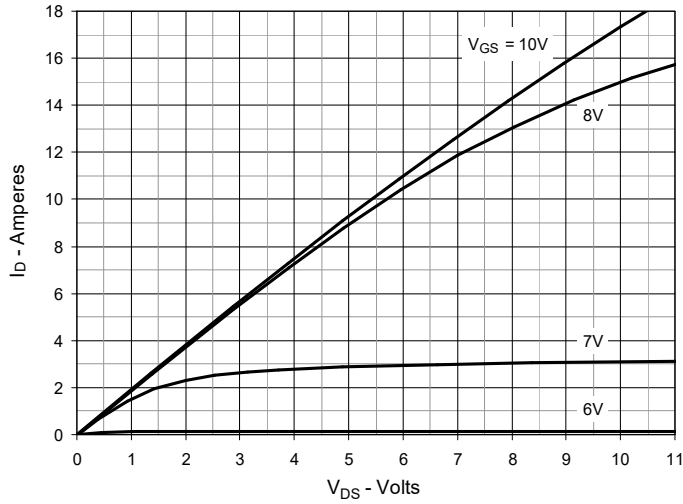
Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

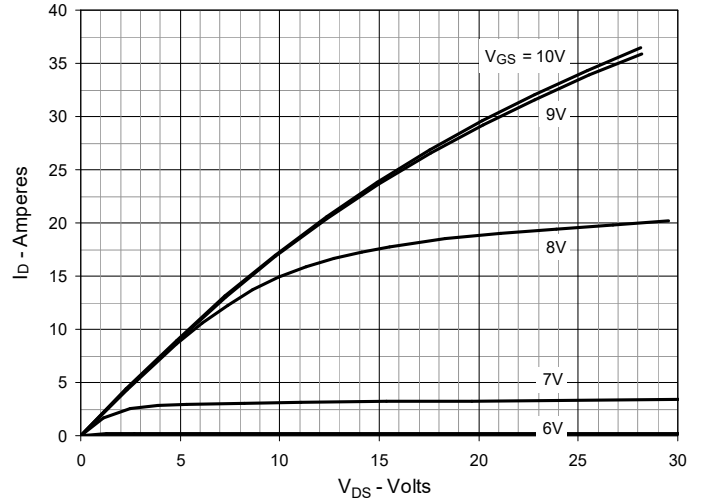
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

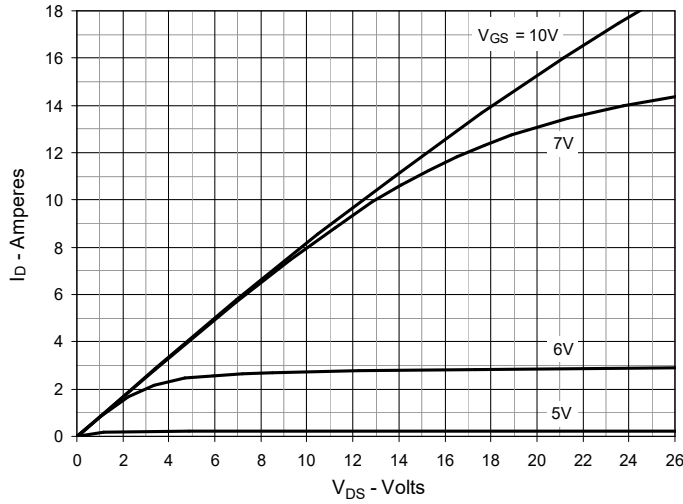
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



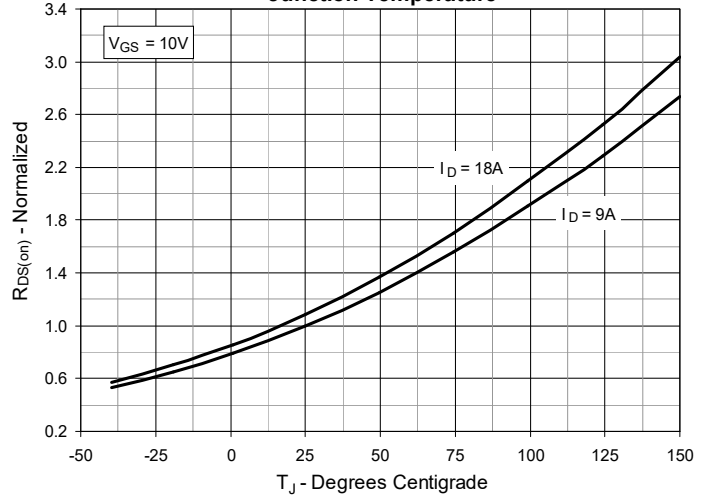
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



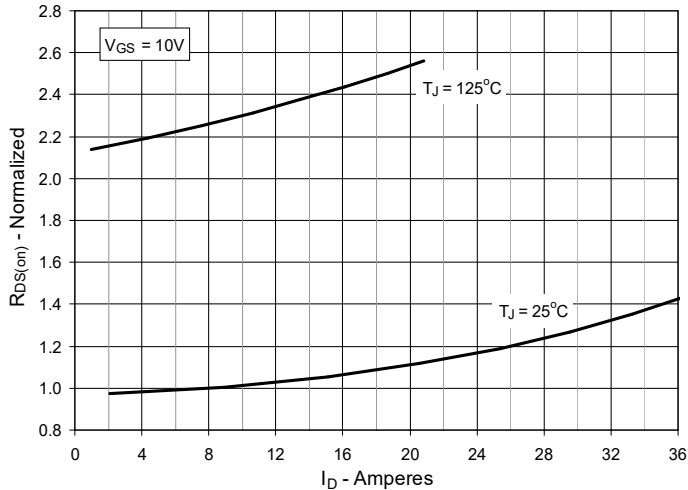
**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$**



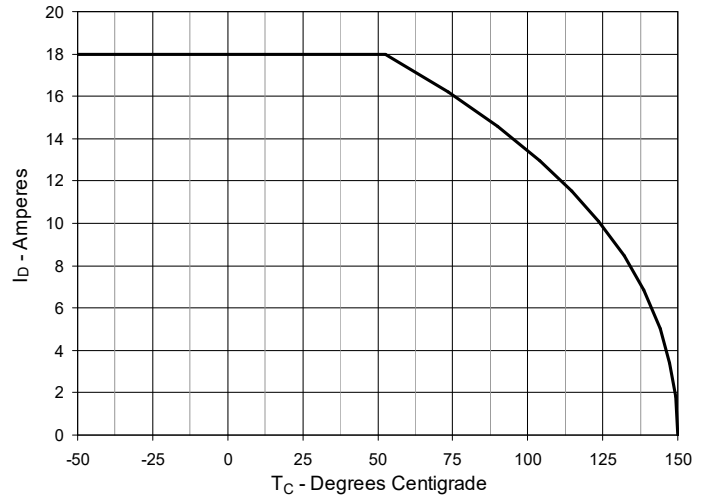
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 9A$  Value vs. Junction Temperature**



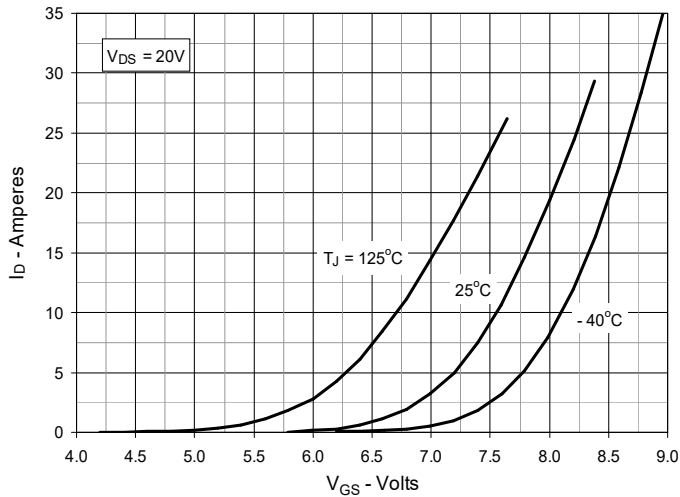
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 9A$  Value vs. Drain Current**



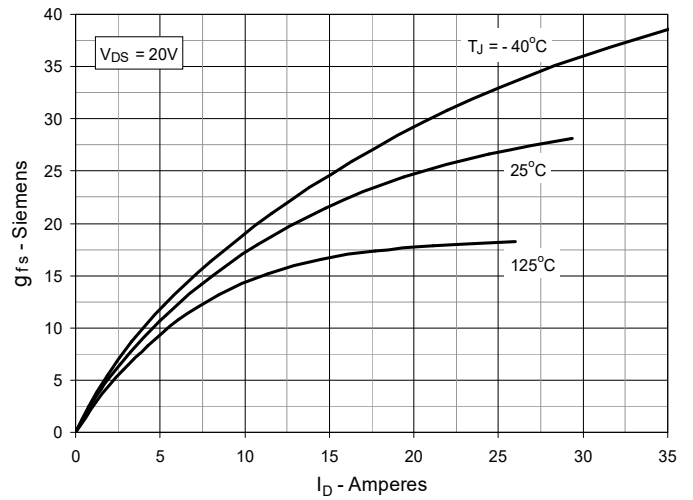
**Fig. 6. Maximum Drain Current vs. Case Temperature**



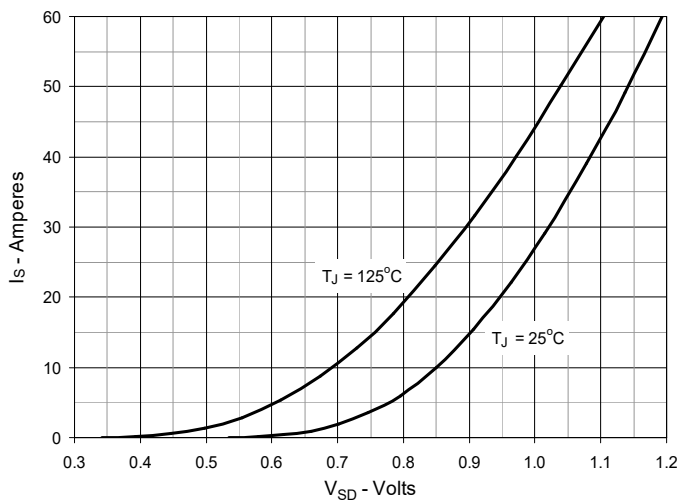
**Fig. 7. Input Admittance**



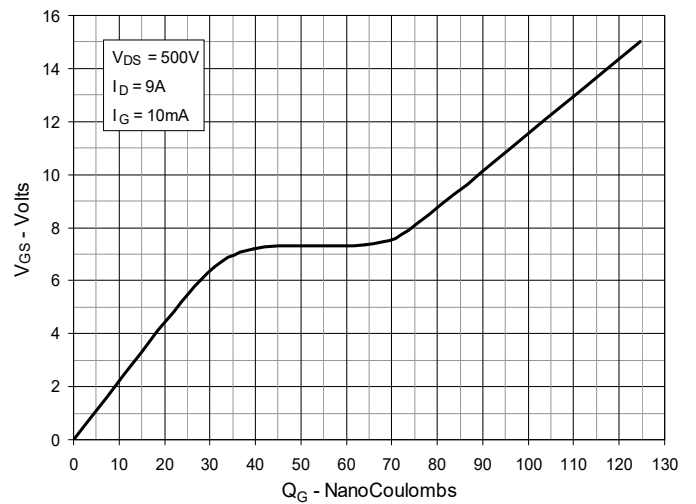
**Fig. 8. Transconductance**



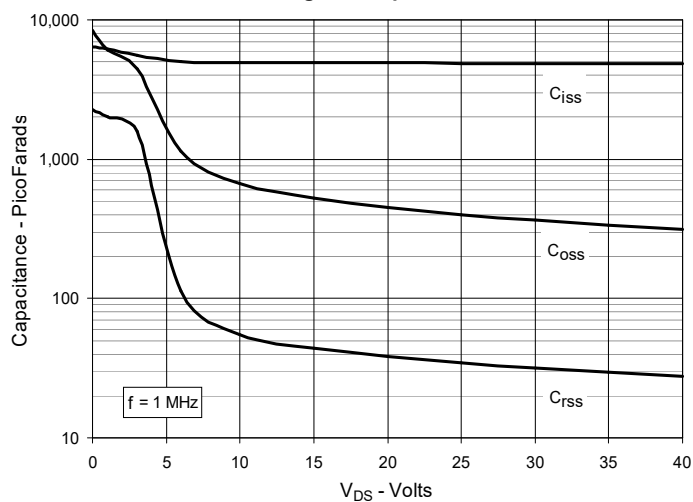
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**

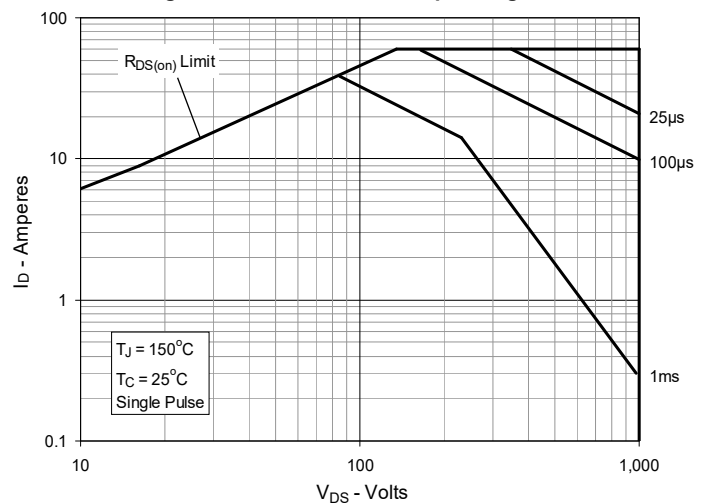
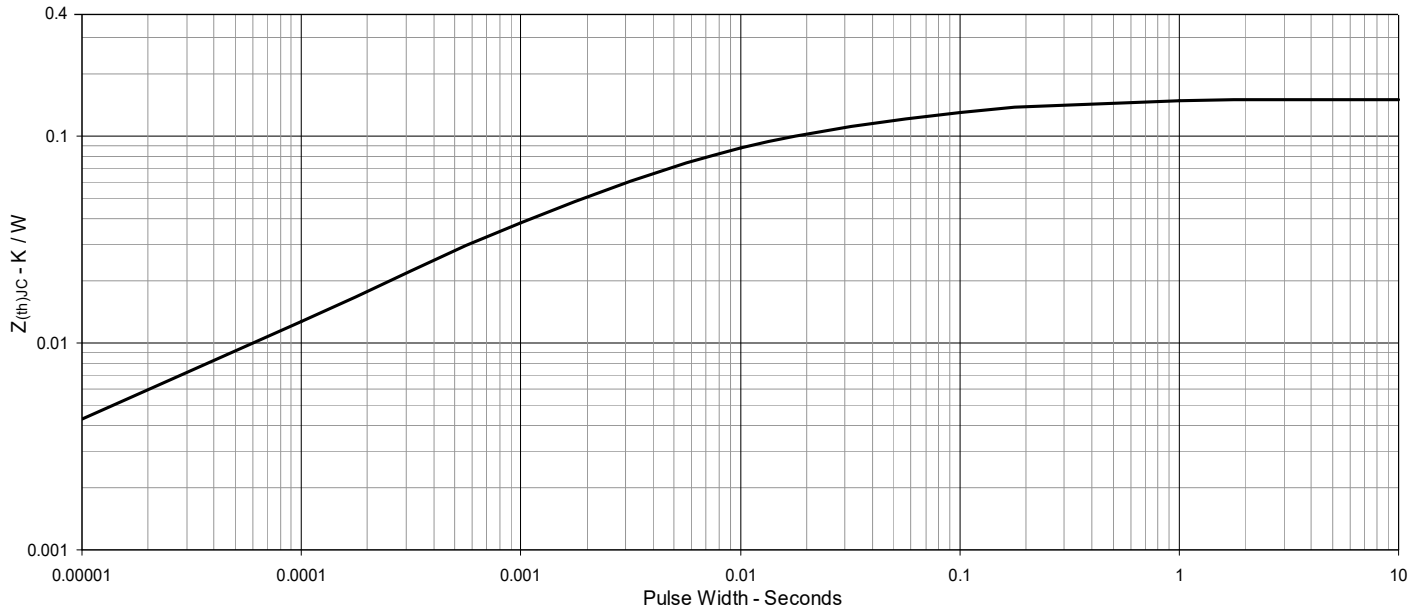
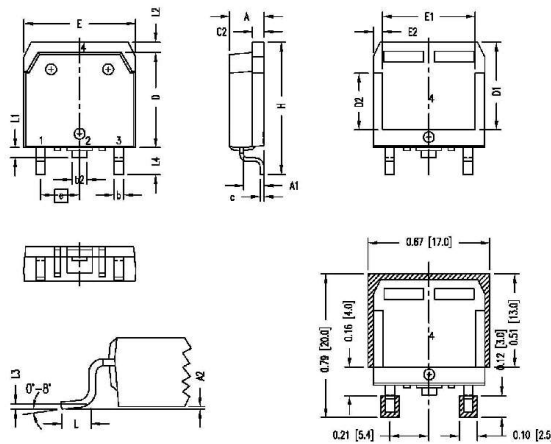


Fig. 13 Maximum Transient Thermal Impedance



**TO-268 Outline**



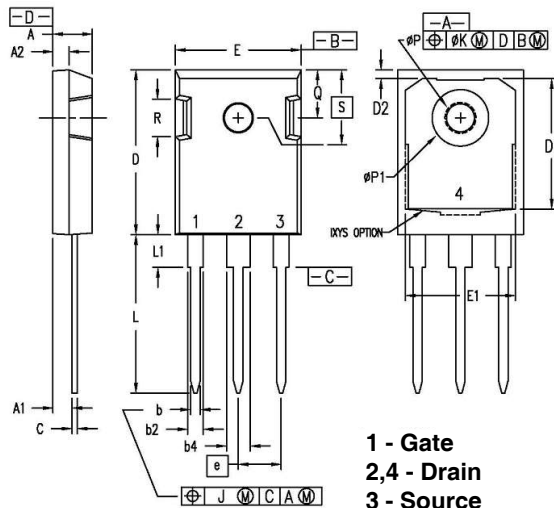
**1 - Gate**  
**2,4 - Drain**  
**3 - Source**

RECOMMENDED MINIMUM FOOT PRINT FOR SMD

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
D2	.320	.335	8.13	8.50
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
E2	.045	.055	1.14	1.39
e	.215	BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010	BSC	0.25	BSC
L4	.150	.161	3.80	4.10

NOTE: ALL METAL SURFACE ARE MATTE PURE TIN PLATED EXCEPT TIRM AREA.  
Pb PLATING THICKNESS (4 - 20 μm)

**TO-247 Outline**



**1 - Gate**  
**2,4 - Drain**  
**3 - Source**

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.690	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.545	.565	13.84	14.35
e	.215	BSC	5.45	BSC
J	--	.010	--	0.25
K	--	.025	--	0.64
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
øP	.140	.144	3.55	3.65
øP1	.275	.290	6.99	7.37
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.242	BSC	6.15	BSC

NOTE: This drawing will meet all dimensions requirement of JEDEC outlines TO-247 AD (R-PSIP-F3)



---

Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).

---